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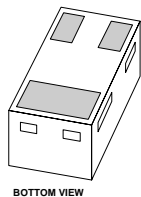
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Kind regards,

Team Nexperia



BOTTOM VIEW

PMBT3906M

40 V, 200 mA PNP switching transistor

Rev. 01 — 22 July 2009

Product data sheet

1. Product profile

1.1 General description

PNP single switching transistor in a SOT883 (SC-101) leadless ultra small Surface-Mounted Device (SMD) plastic package.

NPN complement: PMBT3904M.

1.2 Features

- Single general-purpose switching transistor
- Board-space reduction
- AEC-Q101 qualified
- Ultra small SMD plastic package

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I_C	collector current		-	-	-200	mA
h_{FE}	DC current gain	$V_{CE} = -1$ V; $I_C = -10$ mA	100	180	300	

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base	<p>Transparent top view</p>	<p>sym013</p>
2	emitter		
3	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBT3906M	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.5 mm	SOT883

4. Marking

Table 4. Marking codes

Type number	Marking code
PMBT3906M	6Q

5. Limiting values

Table 5. Limiting values

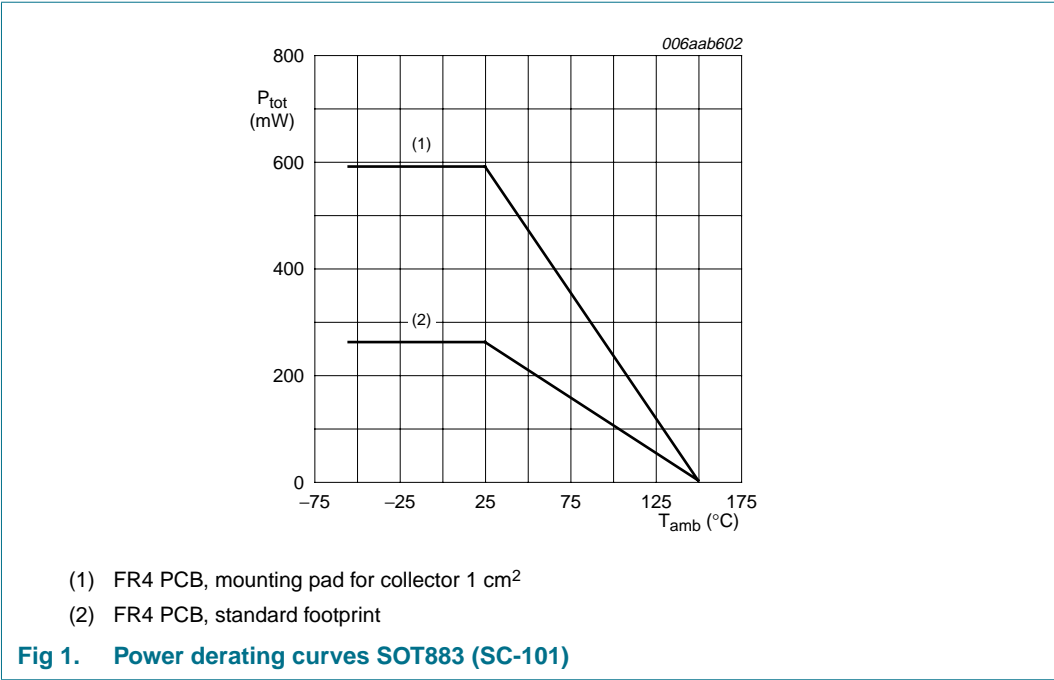
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	−40	V
V _{CEO}	collector-emitter voltage	open base	-	−40	V
V _{EBO}	emitter-base voltage	open collector	-	−6	V
I _C	collector current		-	−200	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	−200	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	−100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1][2] -	260	mW
			[1][3] -	590	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		−55	+150	°C
T _{stg}	storage temperature		−65	+150	°C

[1] Reflow soldering is the only recommended soldering method.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

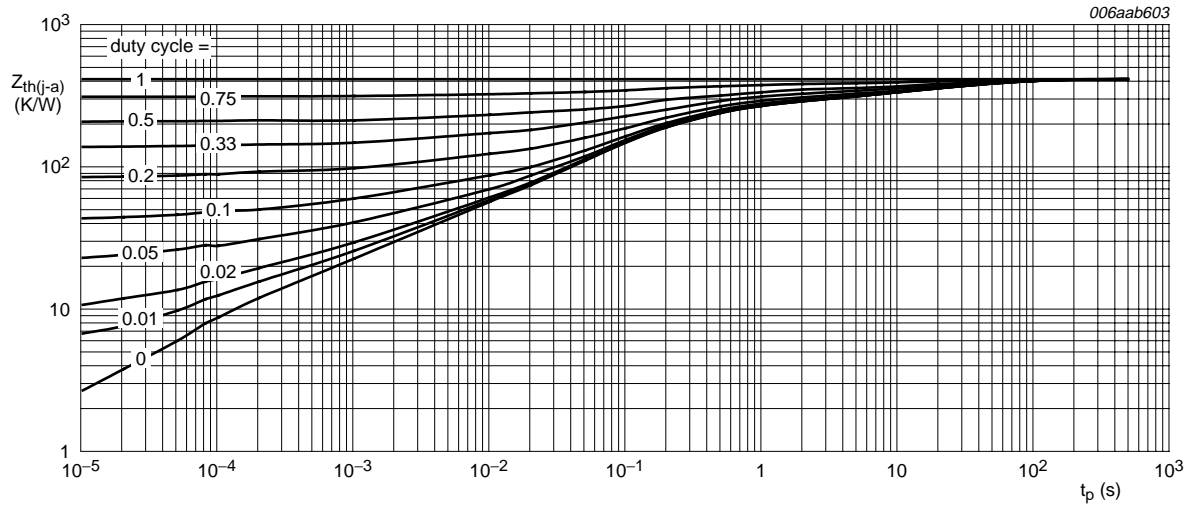


6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	481 K/W
			[1][3]	-	-	212 K/W

- [1] Reflow soldering is the only recommended soldering method.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

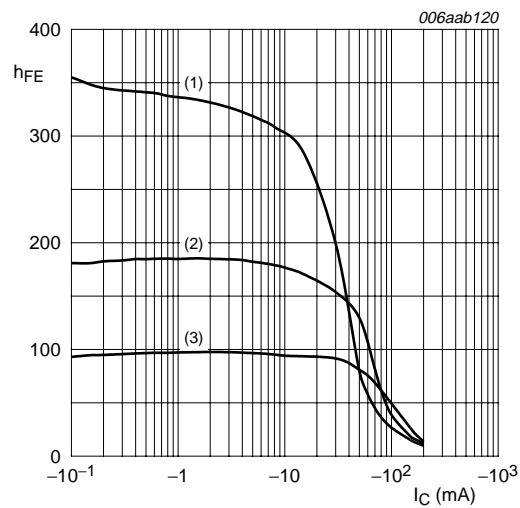
Table 7. Characteristics

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}$	-	-	-50	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -6\text{ V}; I_C = 0\text{ A}$	-	-	-50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$				
		$I_C = -0.1\text{ mA}$	60	180	-	
		$I_C = -1\text{ mA}$	80	180	-	
		$I_C = -10\text{ mA}$	100	180	300	
		$I_C = -50\text{ mA}$	60	130	-	
		$I_C = -100\text{ mA}$	30	50	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	-	-100	-250	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	-	-165	-400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	-	-750	-850	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	-	-850	-950	mV
t_d	delay time	$V_{CC} = -3\text{ V};$	-	-	35	ns
t_r	rise time	$I_C = -10\text{ mA};$	-	-	35	ns
t_{on}	turn-on time	$I_{Bon} = -1\text{ mA};$	-	-	70	ns
		$I_{Boff} = 1\text{ mA}$	-	-	225	ns
t_s	storage time		-	-	75	ns
t_f	fall time		-	-	300	ns
t_{off}	turn-off time		-	-	4.5	pF
C_c	collector capacitance	$V_{CB} = -5\text{ V}; I_E = I_C = 0\text{ A};$ $f = 1\text{ MHz}$	-	-	4.5	pF

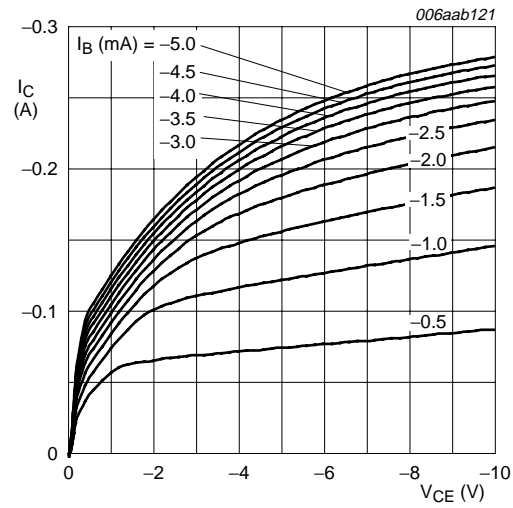
Table 7. Characteristics ...continued
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_e	emitter capacitance	$V_{EB} = -500\text{ mV};$ $I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	-	-	10	pF
f_T	transition frequency	$V_{CE} = -20\text{ V};$ $I_C = -10\text{ mA};$ $f = 100\text{ MHz}$	250	-	-	MHz
NF	noise figure	$V_{CE} = -5\text{ V};$ $I_C = -100\text{ }\mu\text{A}; R_S = 1\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	-	-	4	dB



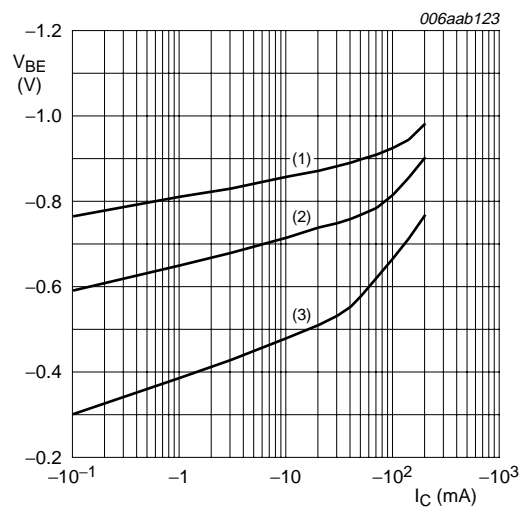
$V_{CE} = -1\text{ V}$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 3. DC current gain as a function of collector current; typical values



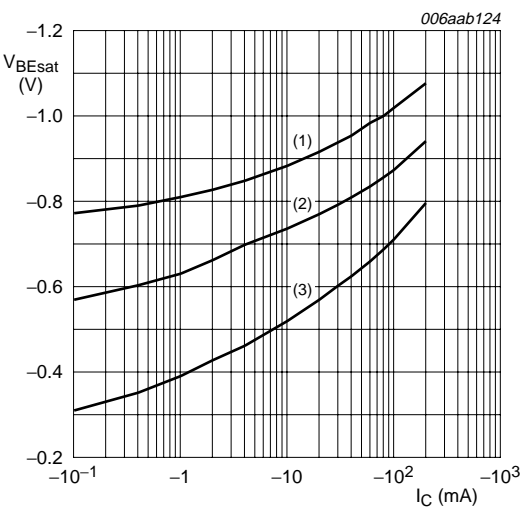
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 4. Collector current as a function of collector-emitter voltage; typical values



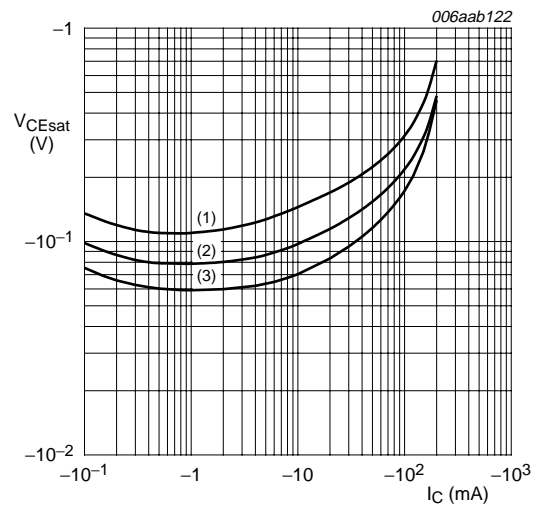
$V_{CE} = -1\text{ V}$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 10$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

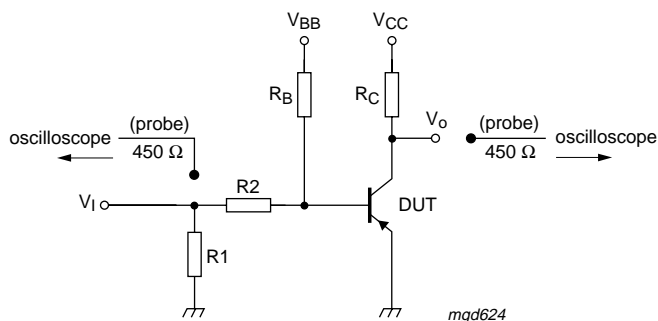
Fig 6. Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 10$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

8. Test information



$V_I = 5 \text{ V}$; $t = 600 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$
 $R_1 = 56 \text{ } \Omega$; $R_2 = 2.5 \text{ k}\Omega$; $R_B = 3.9 \text{ k}\Omega$; $R_C = 270 \text{ } \Omega$
 $V_{BB} = 1.9 \text{ V}$; $V_{CC} = -3 \text{ V}$
 Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega$

Fig 8. Test circuit for switching times

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

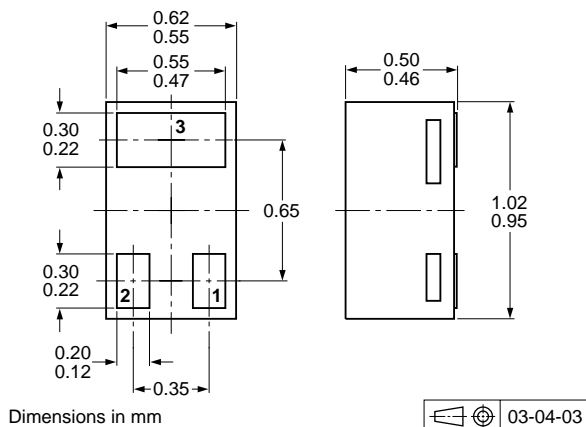


Fig 9. Package outline SOT883 (SC-101)

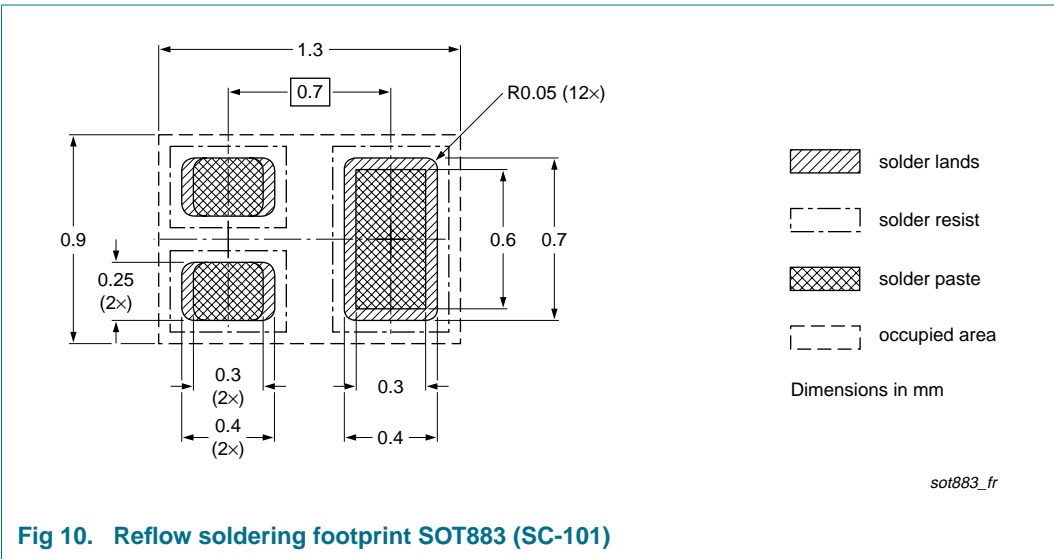
10. Packing information

Table 8. Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity
			10000
PMBT3906M	SOT883	2 mm pitch, 8 mm tape and reel	-315

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering



12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3906M_1	20090722	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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